

2.5V Drive Nch MOSFET

RSU002N06

●Structure

Silicon N-channel MOSFET

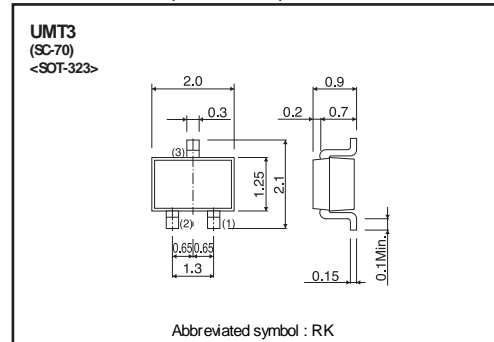
●Features

- 1) High speed switing.
- 2) Small package(UMT3).
- 3) Low voltage drive(2.5V drive).

●Application

Switching

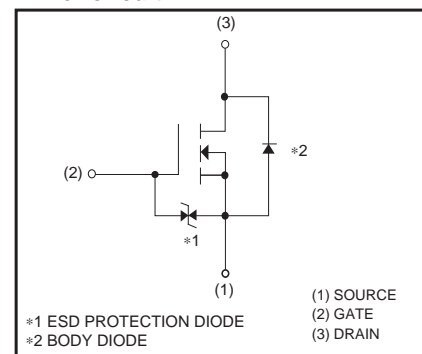
●Dimensions (Unit : mm)



●Packaging specifications

Type	Package	Taping
	Code	T106
	Basic ordering unit (pieces)	3000
RSU002N06		○

●Inner circuit



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DSS}	60	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	Continuous	I_D	± 250 mA
	Pulsed	I_{DP}^{*1}	± 1 A
Source current (Body Diode)	Continuous	I_S	150 mA
	Pulsed	I_{SP}^{*1}	1 A
Power dissipation	P_D^{*2}	200	mW
Channel temperature	T_{ch}	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 Each terminal mounted on a recommended land.

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th}(ch-a)^*$	625	°C / W

* Each terminal mounted on a recommended land.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=60V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	-	2.3	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	-	1.7	2.4	Ω	$I_D=250mA, V_{GS}=10V$
		-	2.1	3.0		$I_D=250mA, V_{GS}=4.5V$
		-	2.3	3.2		$I_D=250mA, V_{GS}=4.0V$
		-	3.0	12.0		$I_D=10mA, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	0.25	-	-	S	$I_D=250mA, V_{DS}=10V$
Input capacitance	C_{iss}	-	15	-	pF	$V_{DS}=25V$
Output capacitance	C_{oss}	-	4.5	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	2.0	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	-	3.5	-	ns	$I_D=100mA, V_{DD} \approx 30V$
Rise time	t_r *	-	5	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}$ *	-	18	-	ns	$R_L \approx 300\Omega$
Fall time	t_f *	-	28	-	ns	$R_G=10\Omega$

*Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	-	-	1.2	V	$I_S=250mA, V_{GS}=0V$

*Pulsed

●Electrical characteristic curves

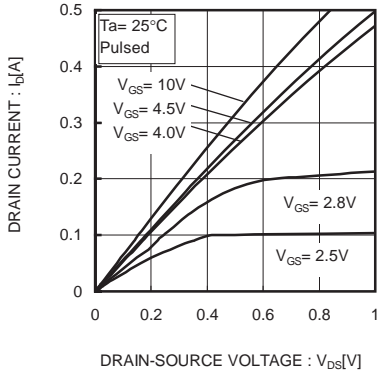


Fig.1 Typical Output Characteristics (I)

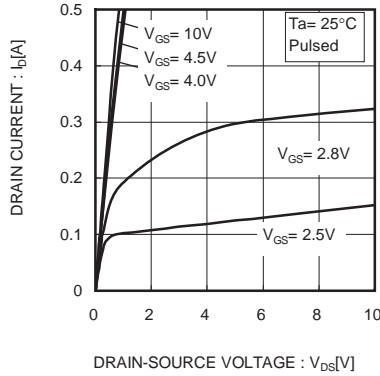


Fig.2 Typical Output Characteristics (II)

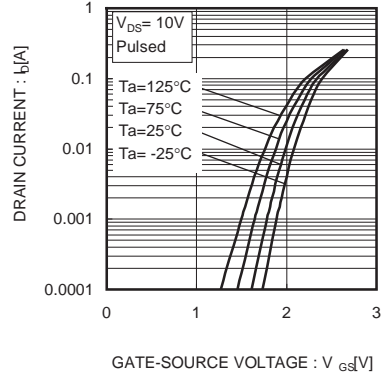


Fig.3 Typical Transfer Characteristics

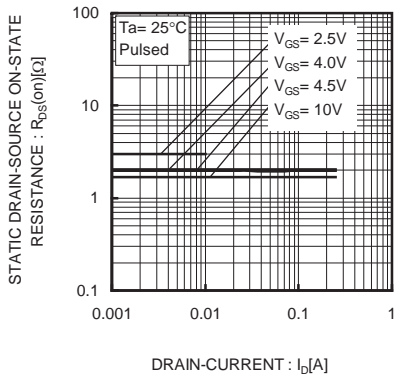


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (I)

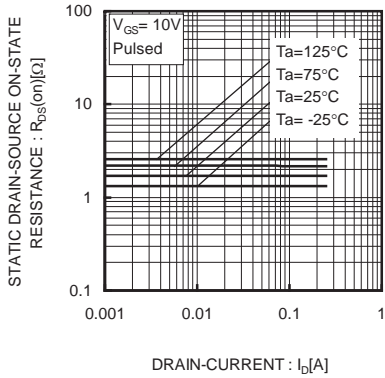


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (II)

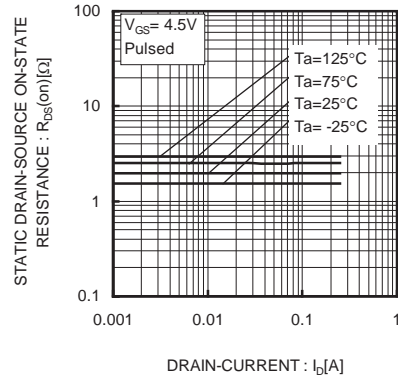


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current (III)

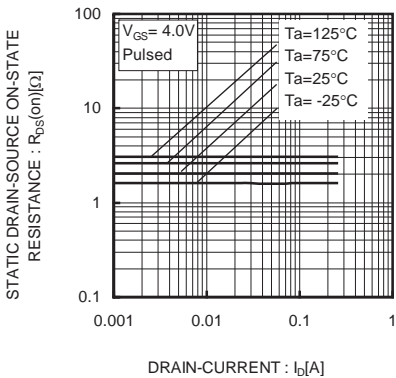


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (IV)

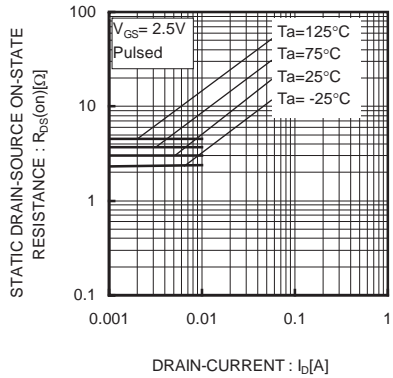


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (IV)

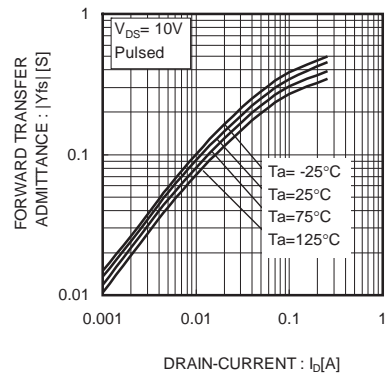


Fig.9 Forward Transfer Admittance vs. Drain Current

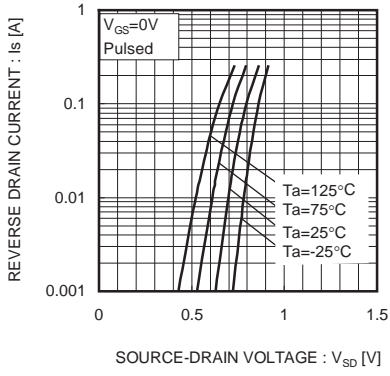


Fig.10 Reverse Drain Current vs. Source-Drain Voltage

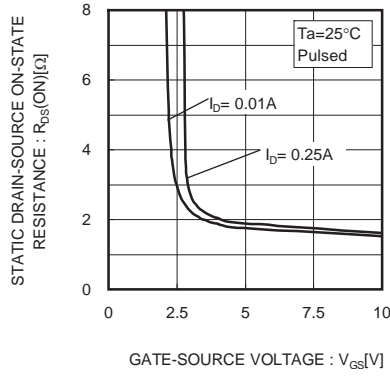


Fig.11 Static Drain-Source On-State Resistance vs. Gate Source Voltage

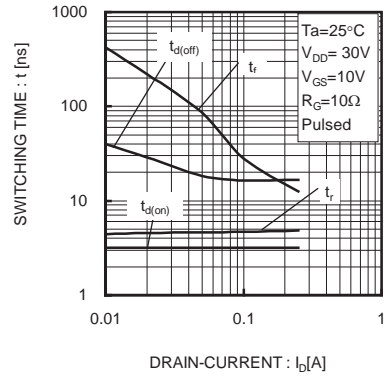


Fig.12 Switching Characteristics

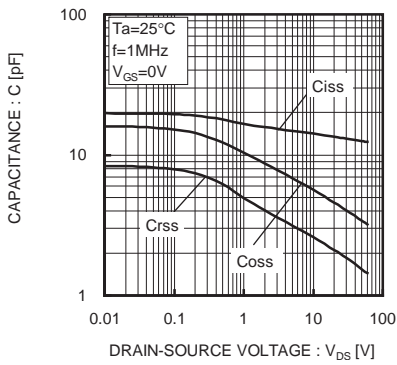


Fig.13 Typical Capacitance vs. Drain-Source Voltage

●Measurement circuits

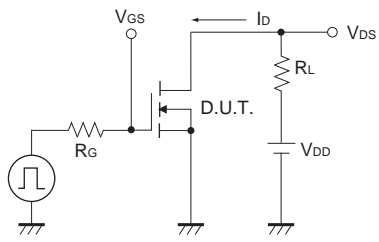


Fig.1-1 Switching time measurement circuit

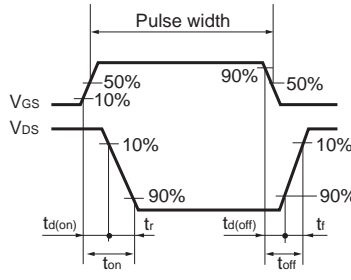


Fig.1-2 Switching waveforms

●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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